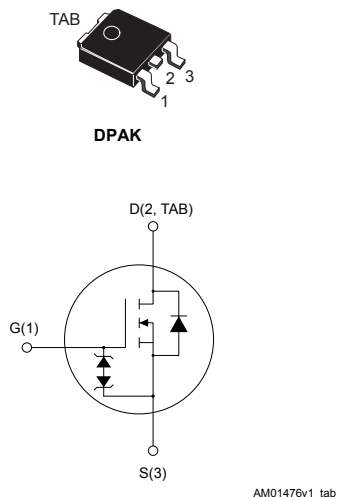


N-channel 1000 V, 5.4 Ω typ., 2.5 A SuperMESH Power MOSFET in a DPAK package



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STD3NK100Z	1000 V	6.0 Ω	2.5 A

- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Zener-protected

Applications

- Switching applications

Description

This high-voltage device is a Zener-protected N-channel Power MOSFET developed using the SuperMESH technology by STMicroelectronics, an optimization of the well-established PowerMESH. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.



Product status link

[STD3NK100Z](#)

Product summary

Order code	STD3NK100Z
Marking	D3NK100Z
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1000	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	2.5	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	1.57	
$I_{DM}^{(1)}$	Drain current (pulsed)	10	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	90	W
ESD	Gate-source, human body model ($R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$)	3	kV
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating junction temperature range		$^{\circ}\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 2.5\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} = 80\%V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.39	$^{\circ}\text{C}/\text{W}$
$R_{thJA}^{(1)}$	Thermal resistance, junction-to-ambient	50	$^{\circ}\text{C}/\text{W}$

1. When mounted on an 1-inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width is limited by T_J max.)	2.5	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	110	mJ

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	1000			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 1000\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 1000\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$			50	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 30\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3.00	3.75	4.50	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.25\text{ A}$		5.4	6.0	Ω

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	601	-	pF
C_{oss}	Output capacitance		-	53	-	pF
C_{rss}	Reverse transfer capacitance		-	12	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ V to } 800\text{ V}$	-	15	-	pF
R_G	Gate input resistance	$f = 1\text{ MHz}$, open drain	-	8.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 800\text{ V}$, $I_D = 2.5\text{ A}$, $V_{GS} = 0\text{ to } 10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	18	-	nC
Q_{gs}	Gate-source charge		-	3.6	-	nC
Q_{gd}	Gate-drain charge		-	9.2	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 500\text{ V}$, $I_D = 1.25\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	15	-	ns
t_r	Rise time		-	7.5	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	39	-	ns
t_f	Fall time		-	32	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		10	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5 \text{ A}$, $V_{GS} = 0 \text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100 \text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	584		ns
Q_{rr}	Reverse recovery charge		-	2.3		μC
I_{RRM}	Reverse recovery current		-	8		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	628		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current		-	8.1		A

1. Pulse width is limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

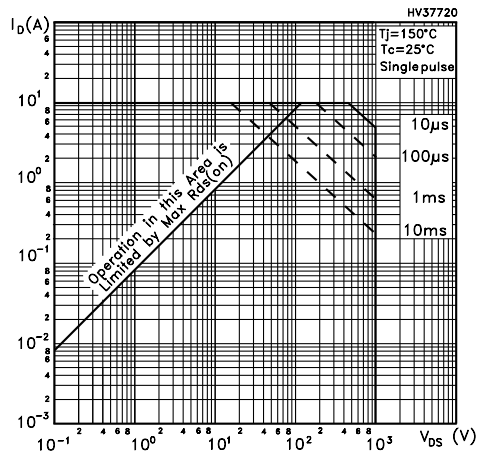
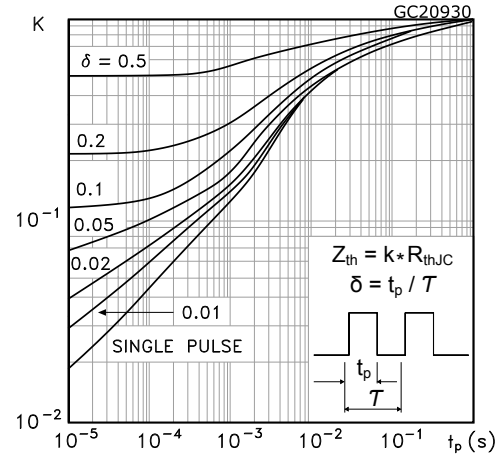
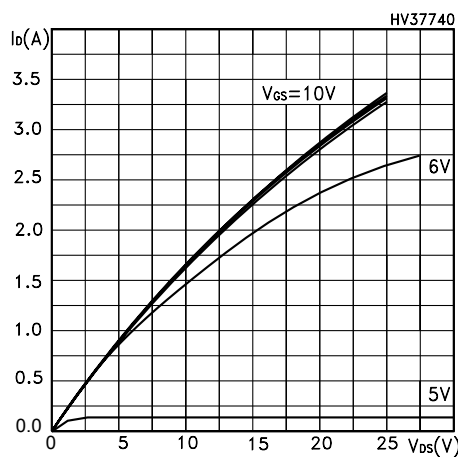
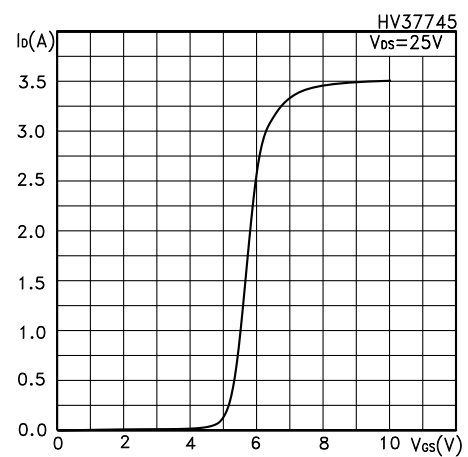
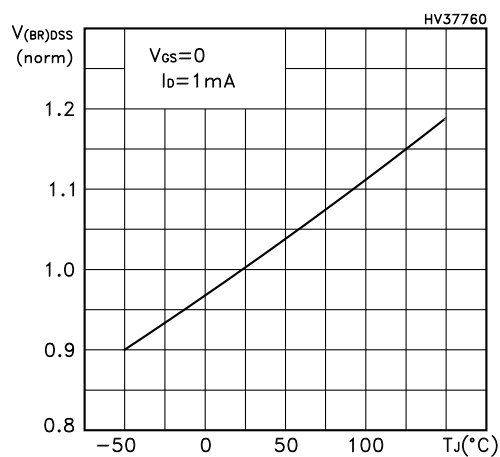
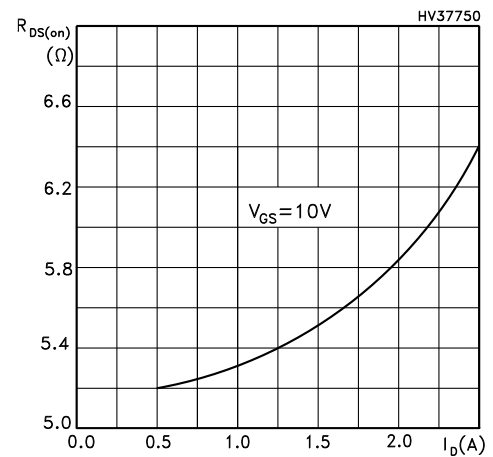
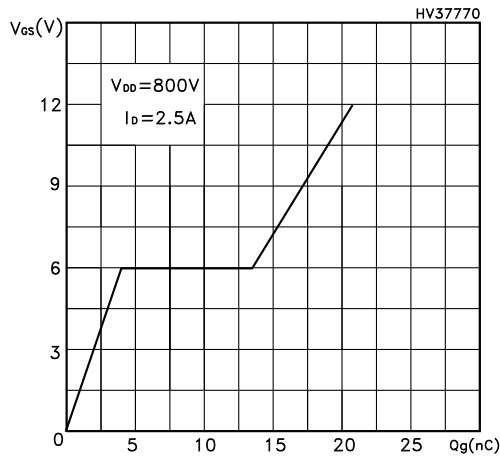
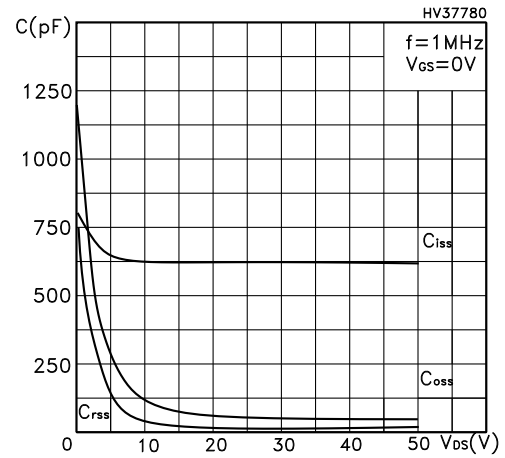
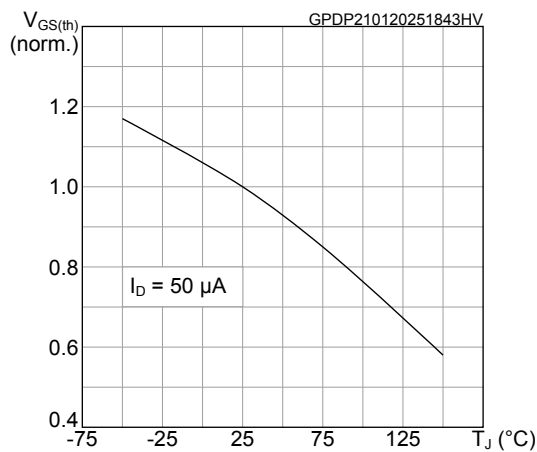
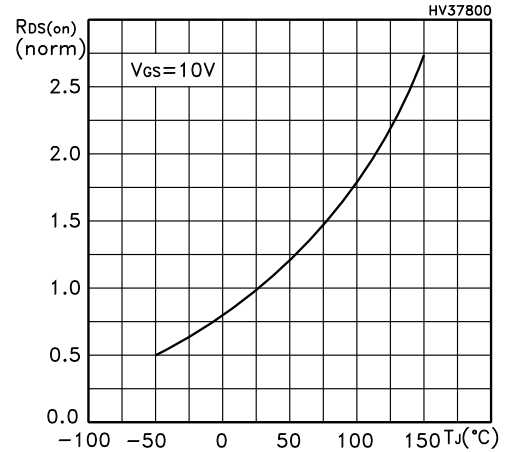
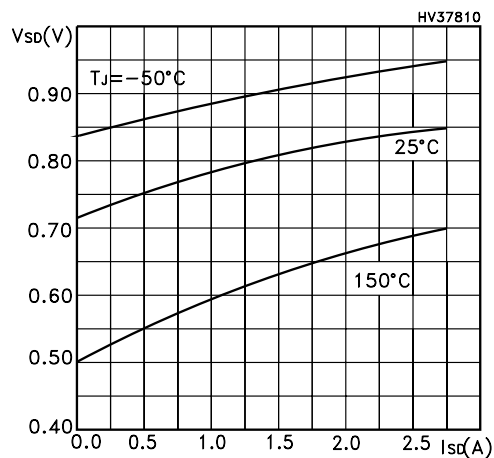
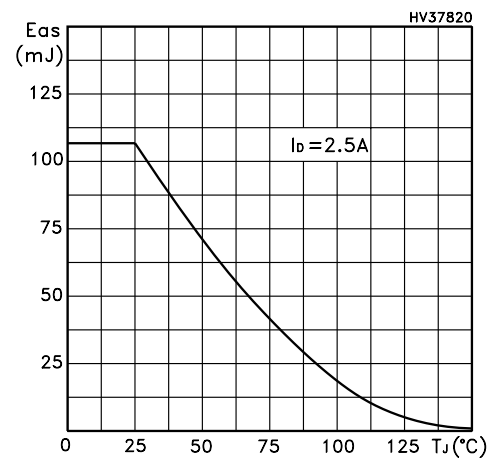
Figure 1. Safe operating area

Figure 2. Thermal impedance

Figure 3. Output characteristics

Figure 4. Transfer characteristics

Figure 5. Normalized $V_{(BR)DSS}$ vs temperature

Figure 6. Static drain-source on resistance


Figure 7. Gate charge vs gate-source voltage

Figure 8. Capacitance variations

Figure 9. Normalized gate threshold vs temperature

Figure 10. Normalized on resistance vs temperature

Figure 11. Source-drain diode forward characteristics

Figure 12. Maximum avalanche energy vs temperature


3 Test circuits

Figure 13. Test circuit for resistive load switching times



AM01468v1

Figure 14. Test circuit for gate charge behavior



AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



AM01470v1

Figure 16. Unclamped inductive load test circuit



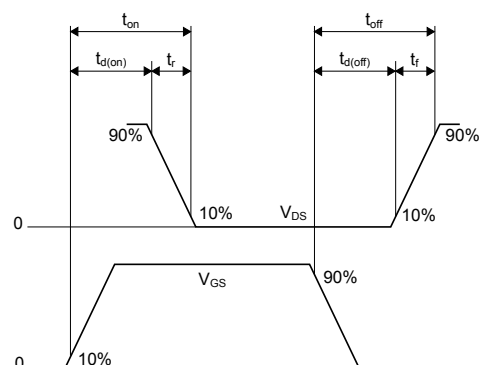
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Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



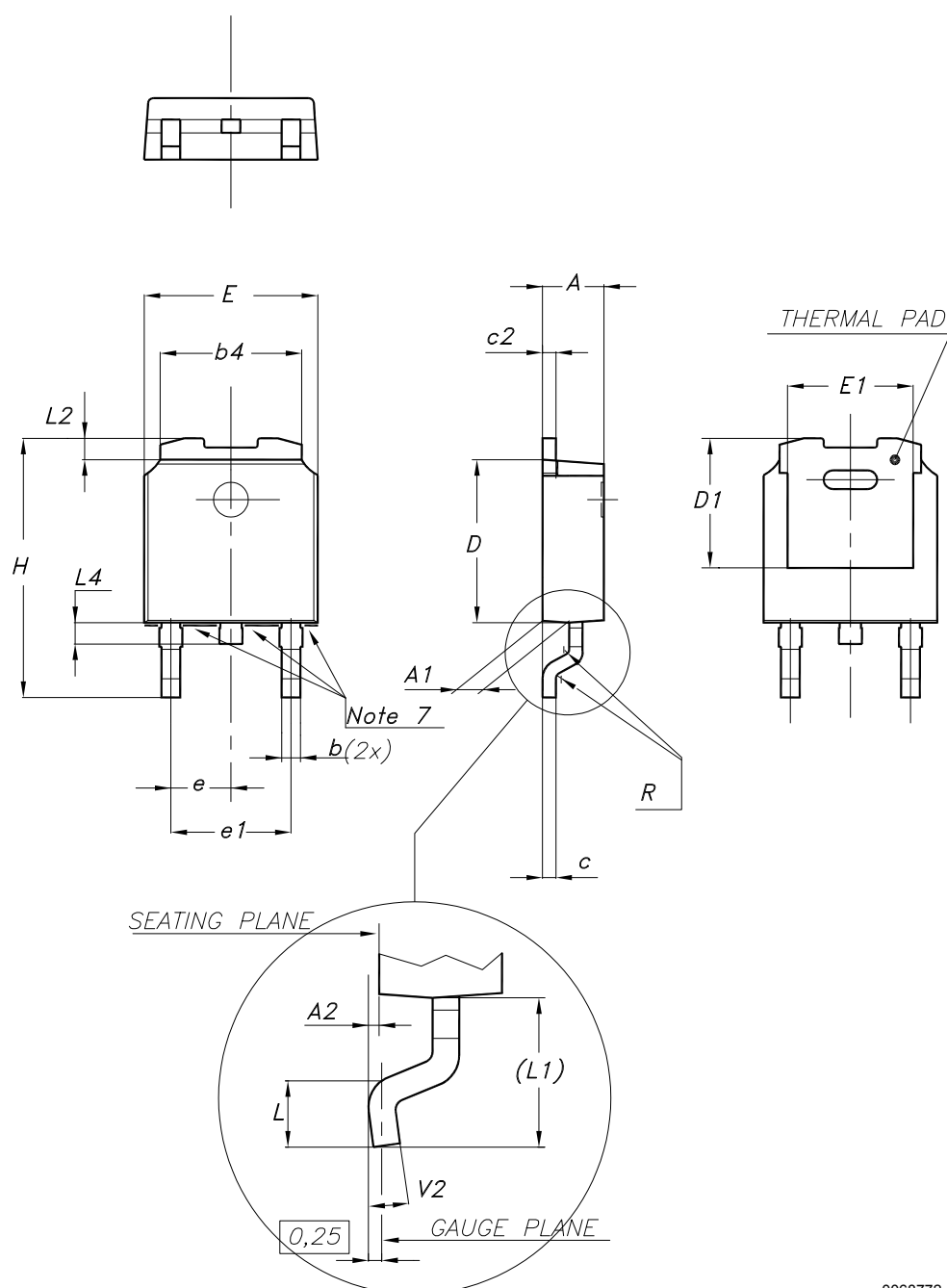
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 19. DPAK (TO-252) type A2 package outline



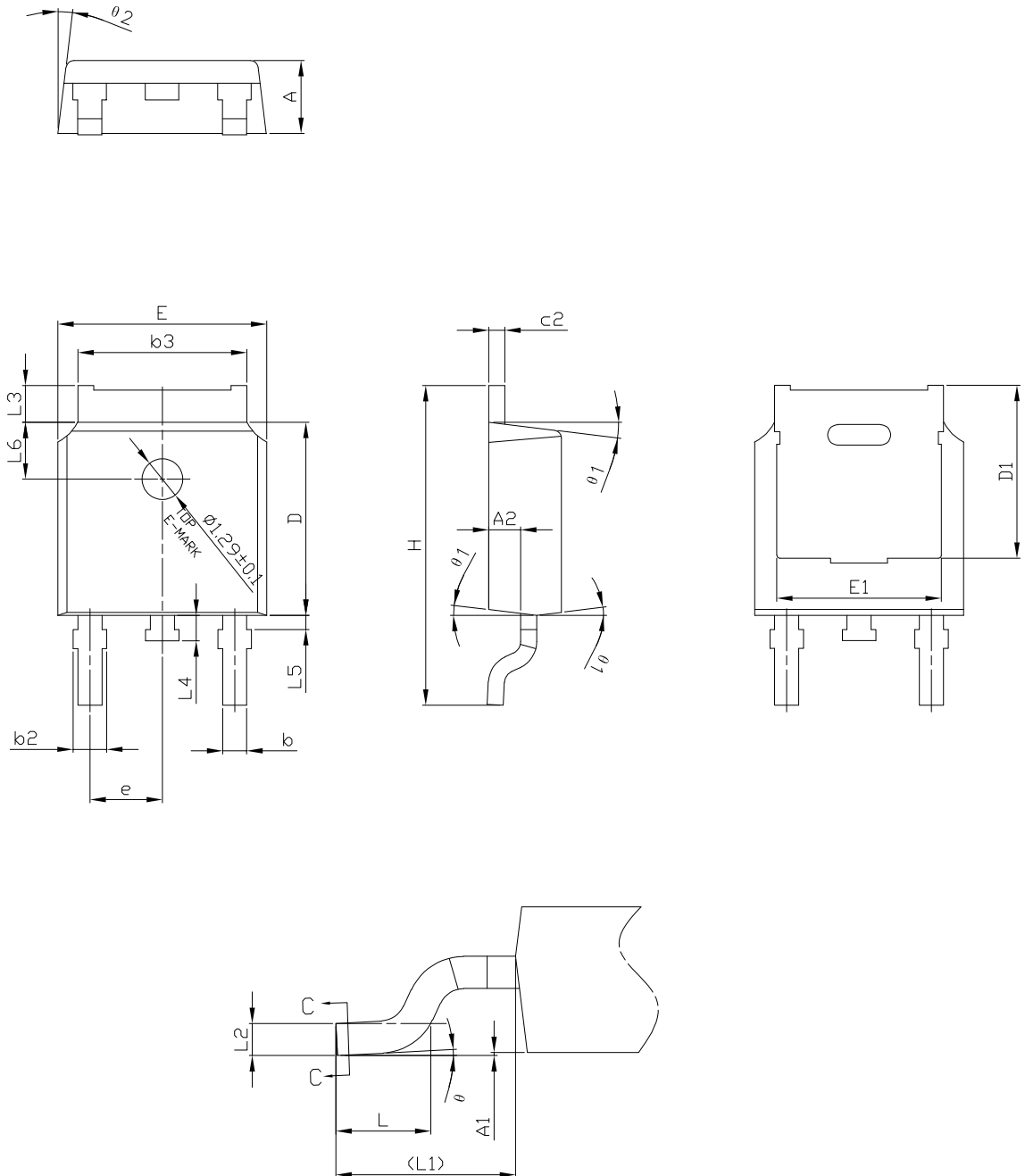
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Table 8. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C3 package information

Figure 20. DPAK (TO-252) type C3 package outline



0068772_type-C3_rev34

Table 9. DPAK (TO-252) type C3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.00		0.10
A2	0.90	1.01	1.10
b	0.72		0.85
b2	0.72		1.10
b3	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.20	5.45	5.70
E	6.50	6.60	6.70
E1	5.00	5.20	5.40
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.51 BSC		
L3	0.90		1.25
L4	0.60	0.80	1.00
L5	0.15		0.75
L6	1.80 REF		
θ	0°		8°
θ1	5°	7°	9°
θ2	5°	7°	9°

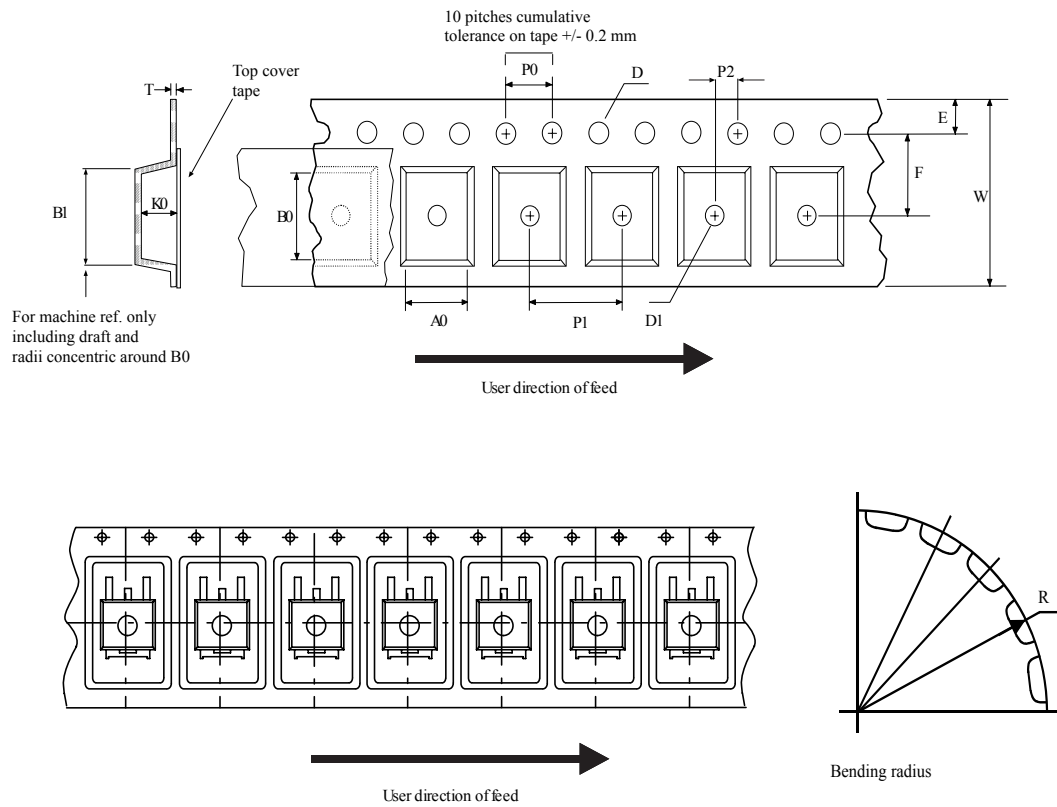
Technical drawing of a mechanical part. The drawing shows a top view and a side view. The top view is a rectangle with a width of 6.3 and a height of 6.5. The side view is a rectangle with a width of 11.2 and a height of 1.8 MIN. The part has two rectangular features on the top surface, each with a width of 1.5 and a height of 2.9. The distance between the centers of these features is 4.572. The part is shown with section lines (hatching) indicating the material. The drawing includes dimension lines and arrows indicating the measurement of the features.

2) The device must be positioned within $\oplus 0.05 \text{ A B}$

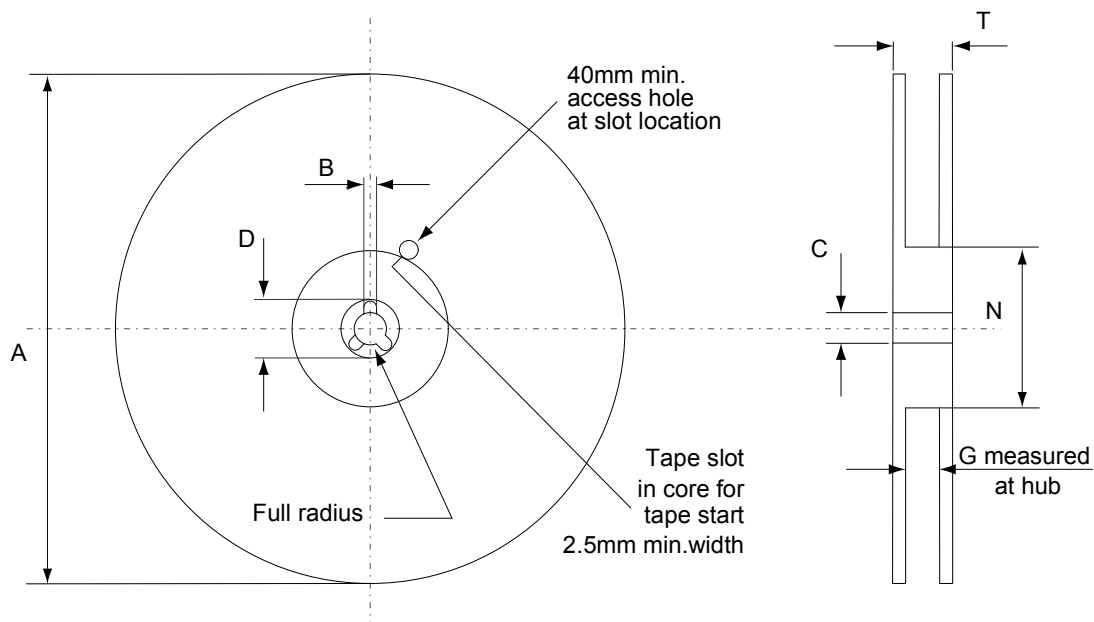
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4.3 DPAK (TO-252) packing information

Figure 22. DPAK (TO-252) tape outline



AM08852v1

Figure 23. DPAK (TO-252) reel outline


AM06038v1

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 11. Document revision history

Date	Revision	Changes
17-May-2007	1	First release
18-Oct-2007	2	Added DPAK
02-Jul-2018	3	The part number STP3NK100Z has been moved to a separate datasheet. Removed maturity status indication from cover page. The document status is production data. Updated title in cover page, <i>Section 1 Electrical ratings</i>, <i>Section 2 Electrical characteristics</i> and <i>Section 4 Package information</i>. Minor text changes.
27-Jun-2023	4	The part number STF3NK100Z have been moved to a separate datasheet and the document has been updated accordingly. Removed "Table 8. Gate-source Zener diode". Updated <i>Section 4.1 DPAK (TO-252) type A2 package information</i> and replaced "<i>Section 4.2 DPAK (TO-252) type C2 package information</i>" with <i>Section 4.2 DPAK (TO-252) type C3 package information</i>. Minor text changes.
27-Jan-2025	5	Updated Figure 9. Normalized gate threshold vs temperature.

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